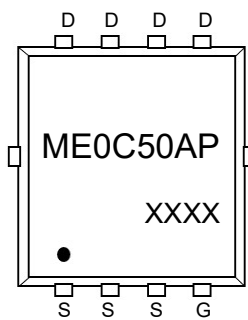


Features

- Excellent $R_{DS(on)}$ and Low Gate Charge
- Extremely low switching loss
- Excellent stability and uniformity

Application

- Power management
- Portable equipment

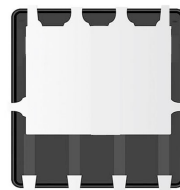


ME0C50AP: Device code
XXXX : Code

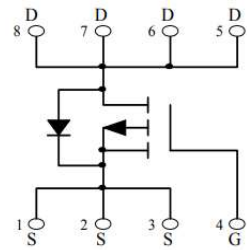
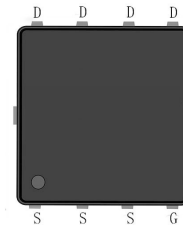
Marking and pin assignment

-20V/-50A P-Channel MOSFET Product Summary

V_{DS}	$R_{DS(on)}$ MAX	I_D MAX
-20V	7.5mΩ@-4.5V	-50A
	10mΩ@-2.5V	



PDFN3X3-8L view



Schematic diagram

Absolute Maximum Ratings (TA=25°C unless otherwise noted)				
Symbol	Parameter		Rating	Unit
Common Ratings (TC=25°C Unless Otherwise Noted)				
V _{DS}	Drain-Source Breakdown Voltage		-20	V
V _{GS}	Gate-Source Voltage		±10	V
T _J	Maximum Junction Temperature		150	°C
T _{STG}	Storage Temperature Range		-50 to 155	°C
I _S	Diode Continuous Forward Current	Tc=25°C	-50	A
Mounted on Large Heat Sink				
I _{DM}	Pulse Drain Current Tested	Tc=25°C	-200	A
I _D	Continuous Drain Current	Tc=25°C	-50	A
P _D	Maximum Power Dissipation	Tc=25°C	42	W
R _{θJA}	Thermal Resistance Junction-Ambient		55	°C/W

Electrical Characteristics (TJ=25°C unless otherwise noted)						
Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ TJ = 25°C (unless otherwise stated)						
BV _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250μA	-20	--	--	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-20V, V _{GS} =0V	--	--	-1	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±10V, V _{DS} =0V	--	--	±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250μA	-0.4	-0.65	-1.0	V
R _{DS(on)}	Drain-Source On-State Resistance	V _{GS} =-4.5V, I _D =-15A	--	5.5	7.5	mΩ
		V _{GS} =-2.5V, I _D =-10A	--	7.5	10	mΩ
Dynamic Electrical Characteristics @ TJ = 25°C (unless otherwise stated)						
C _{ISS}	Input Capacitance	V _{DS} =-10V, V _{GS} =0V, f=1MHz	--	2839	--	pF
C _{OSS}	Output Capacitance		--	372	--	pF
C _{RSS}	Reverse Transfer Capacitance		--	311	--	pF
Switching Characteristics						
Q _g	Total Gate Charge	V _{DS} =-10V, I _D =-15A, V _{GS} =-10V	--	54	--	nC
Q _{gs}	Gate Source Charge		--	7	--	nC
Q _{gd}	Gate Drain Charge		--	14	--	nC
t _{d(on)}	Turn-on Delay Time	V _{DD} =-10V, I _D =-13A, V _{GS} =-10V, R _G =3Ω	--	13	--	nS
t _r	Turn-on Rise Time		--	105	--	nS
t _{d(off)}	Turn-Off Delay Time		--	145	--	nS
t _f	Turn-Off Fall Time		--	150	--	nS
Source- Drain Diode Characteristics						
V _{SD}	Forward on voltage	Tj=25°C, Is=-15A	--	--	-1.2	V

Typical Operating Characteristics

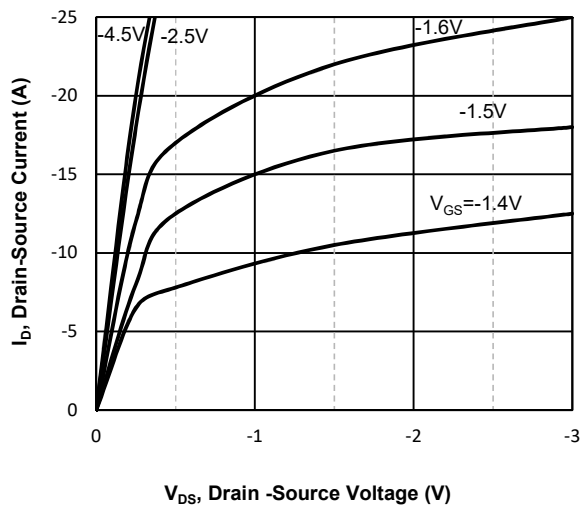


Fig1. Typical Output Characteristics

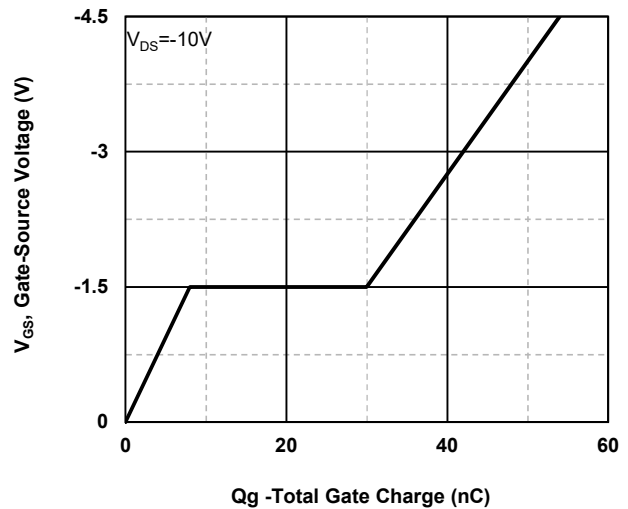


Fig2. Typical Gate Charge Vs. Gate-Source Voltage

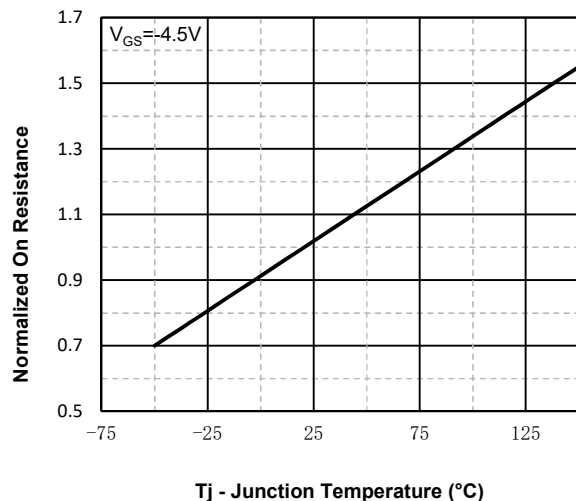


Fig3. Normalized On-Resistance Vs. Temperature

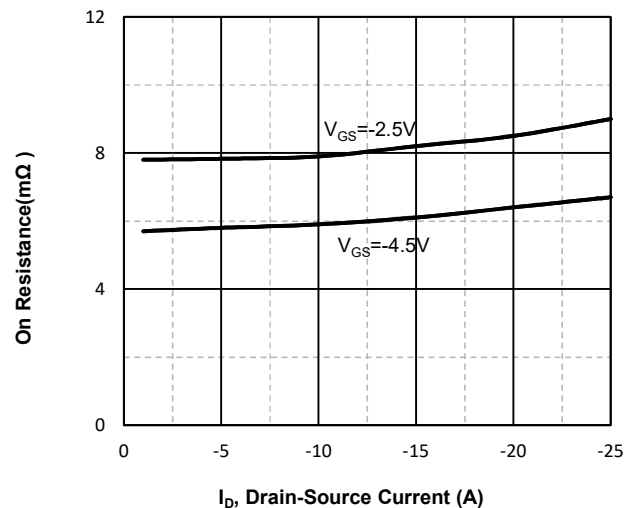


Fig4. On-Resistance Vs. Drain-Source Current

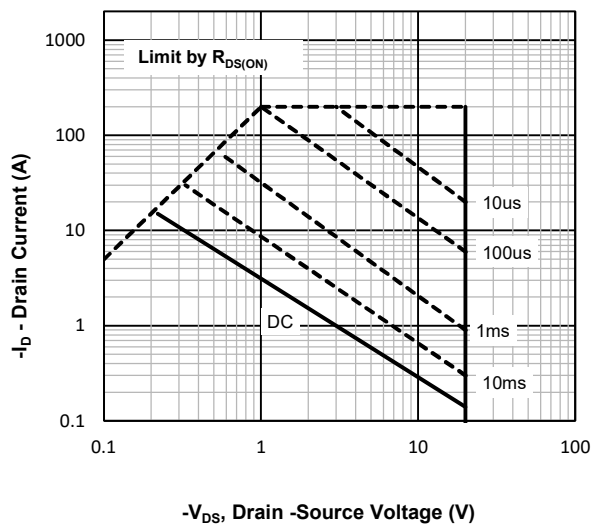


Fig5. Maximum Safe Operating Area

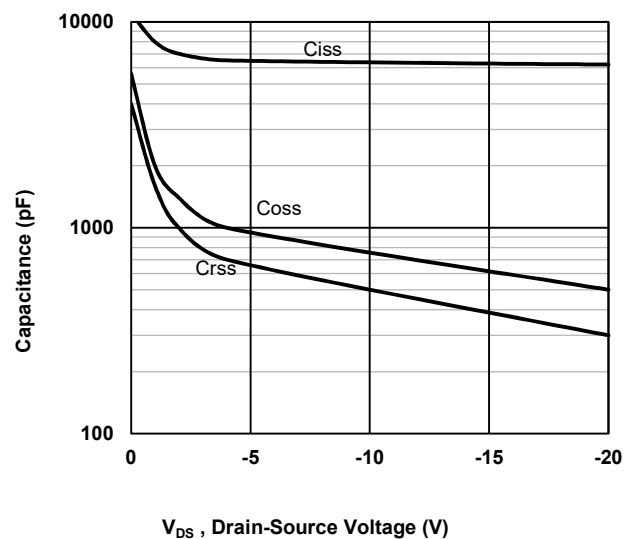
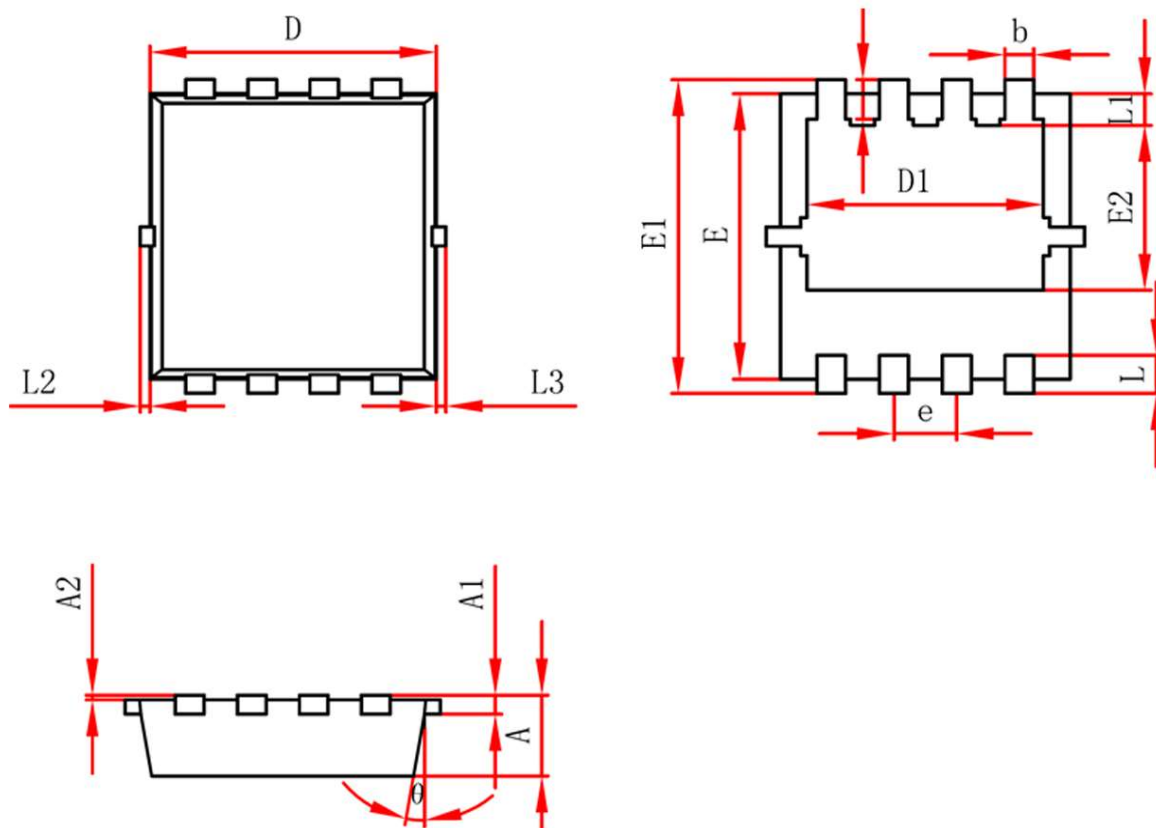


Fig6 Typical Capacitance Vs. Drain-Source Voltage

PDFN3X3-8L Package information


Symbol	Dimensions in Millimeters(mm)		Dimensions In Inches	
	Min	Max	Min	Max
A	0.750	0.850	0.030	0.034
A1	0.152 REF.		0.006 REF.	
A2	0~0.05		0~0.002	
D	2.950	3.150	0.117	0.125
D1	2.400	2.500	0.095	0.099
E	2.950	3.050	0.117	0.121
E1	3.250	3.350	0.129	0.132
E2	1.685	1.785	0.067	0.071
b	0.250	0.350	0.010	0.014
e	0.600	0.700	0.024	0.028
L	0.350	0.450	0.014	0.018
L1	0.325	0.425	0.013	0.017
L2	0~0.100		0~0.004	
L3	0~0.100		0~0.004	
H	0.365	0.465	0.014	0.018
θ	10°	12°	10°	12°